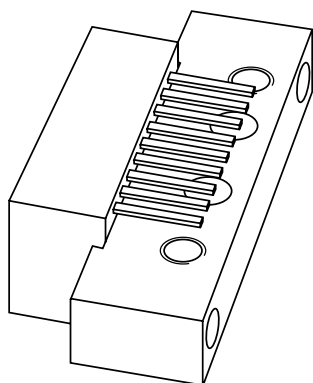


DATA SHEET



BGD885

860 MHz, 17 dB gain power
doubler amplifier

Product specification
Supersedes data of 2001 Oct 25

2001 Nov 02

860 MHz, 17 dB gain power doubler amplifier

BGD885

FEATURES

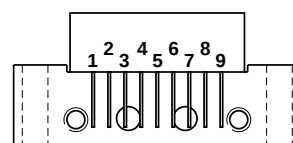
- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

DESCRIPTION

Hybrid amplifier module for CATV/MATV systems operating over a frequency range of 40 to 860 MHz at a voltage supply of 24 V (DC).

PINNING - SOT115D

PIN	DESCRIPTION
1	input
2, 3, 5, 6, 7	common
4	10 V, 200 mA supply terminal
8	+V _B
9	output



Side view

MBK049

Fig.1 Simplified outline.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz	16.5	17.5	dB
I _{tot}	total current consumption (DC)	V _B = 24 V	—	450	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _B	DC supply voltage	—	26	V
V _i	RF input voltage	—	65	dBmV
T _{stg}	storage temperature	−40	+100	°C
T _{mb}	operating mounting base temperature	−20	+100	°C

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CHARACTERISTICS

Table 1 Bandwidth 40 to 860 MHz; $V_B = 24$ V; $T_{mb} = 35$ °C; $Z_S = Z_L = 75$ Ω

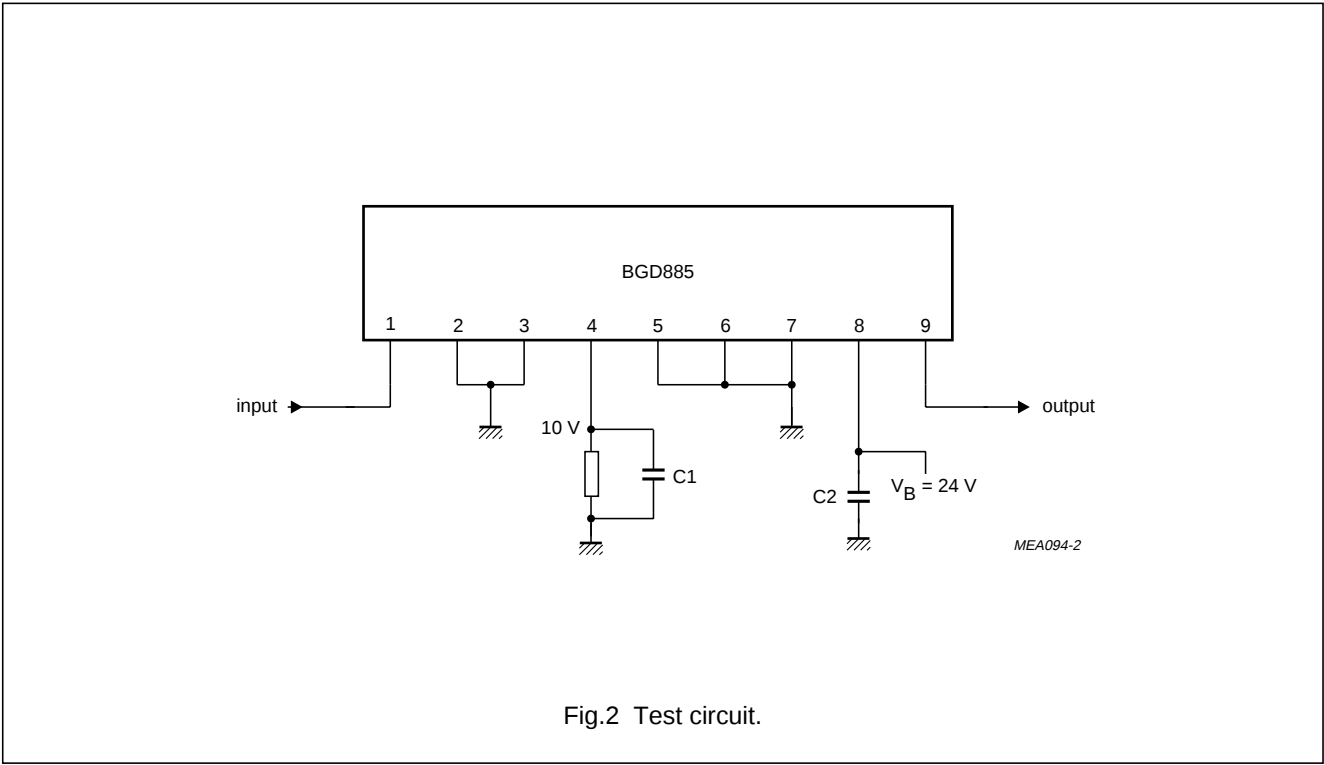
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G_p	power gain	$f = 50$ MHz	16.5	17.5	dB
SL	slope cable equivalent	$f = 40$ to 860 MHz	0.2	1.6	dB
FL	flatness of frequency response	$f = 40$ to 860 MHz	–	± 0.5	dB
S_{11}	input return losses	$f = 40$ MHz; note 1	20	–	dB
		$f = 800$ to 860 MHz	10	–	dB
S_{22}	output return losses	$f = 40$ MHz; note 1	20	–	dB
		$f = 800$ to 860 MHz	10	–	dB
d_2	second order distortion	note 2	–	–53	dB
V_o	output voltage	$d_{im} = -60$ dB; note 3	64	–	dBmV
		$d_{im} = -60$ dB; note 4	63	–	dBmV
F	noise figure	$f = 50$ MHz	–	8	dB
		$f = 550$ MHz	–	8	dB
		$f = 650$ MHz	–	8	dB
		$f = 750$ MHz	–	8	dB
		$f = 860$ MHz	–	8	dB
I_{tot}	total current consumption (DC)	note 5	–	450	mA

Notes

- Decrease per octave of 1.5 dB.
- $V_p = 59$ dBmV at $f_p = 349.25$ MHz;
 $V_q = 59$ dBmV at $f_q = 403.25$ MHz;
measured at $f_p + f_q = 752.5$ MHz.
- Measured according to DIN45004B:
 $f_p = 341.25$ MHz; $V_p = V_o$;
 $f_q = 348.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 350.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 339.25$ MHz.
- Measured according to DIN45004B:
 $f_p = 851.25$ MHz; $V_p = V_o$;
 $f_q = 858.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 860.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 849.25$ MHz.
- The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 30 V.

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List of components (see Fig.2)

COMPONENT	DESCRIPTION	VALUE
C1	ceramic multilayer capacitor	1 nF (max.)
C2	ceramic multilayer capacitor	1 nF
R	resistor	56 Ω , 2 W

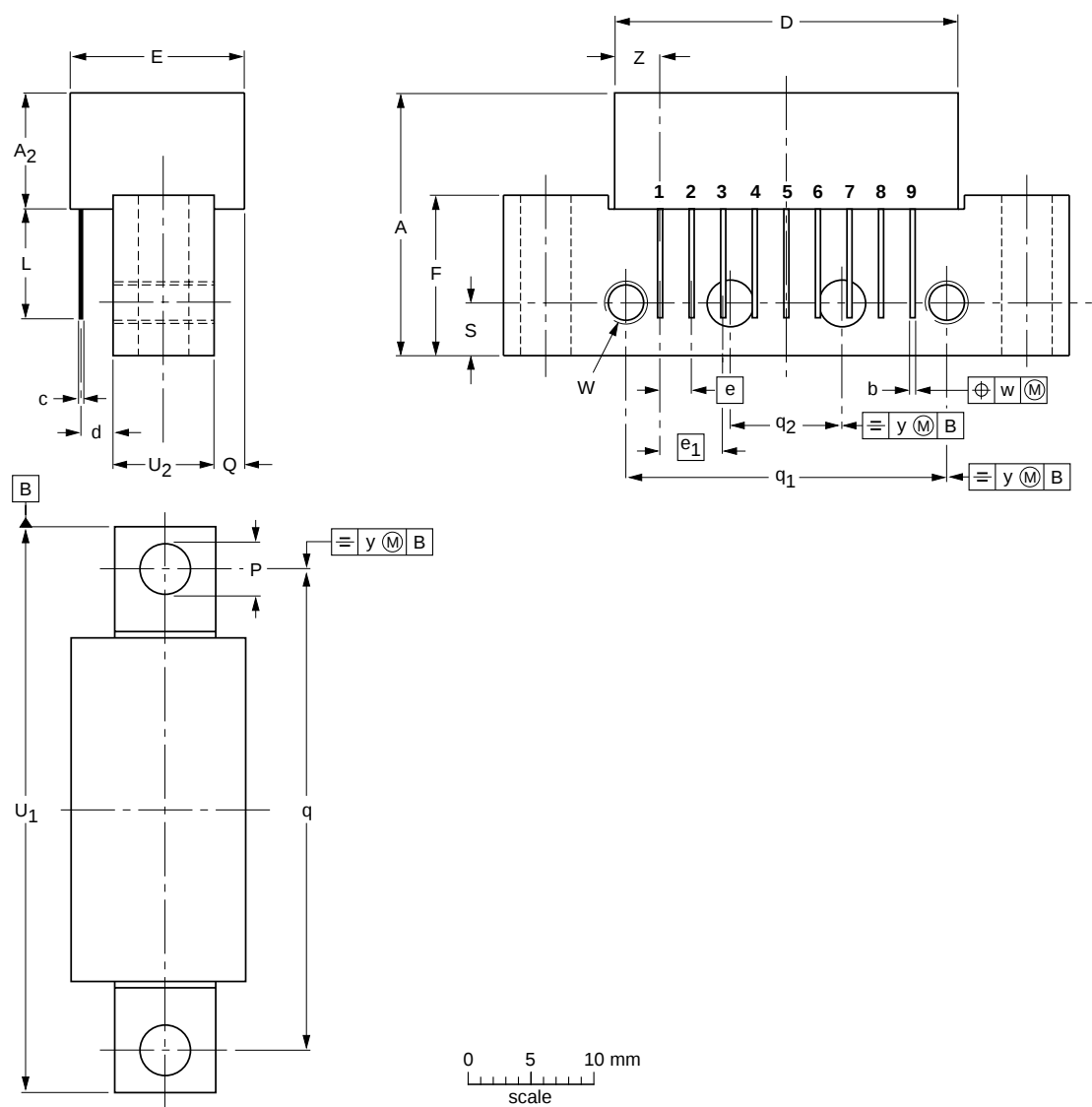
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PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes;
2 x 6-32 UNC and 2 extra horizontal mounting holes; 9 gold-plated in-line leads

SOT115D



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₂ max.	b	c	D max.	d max.	E max.	e	e ₁	F	L min.	∅ P	Q max.	q	q ₁	q ₂	S	U ₁ max.	U ₂	W	w	y	Z max.
mm	20.8	9.1	0.51 0.38	0.25	27.2	2.54	13.75	2.54	5.08	12.7	8.8	4.15 3.85	2.4	38.1	25.4	10.2	4.2	44.75	8	6-32 UNC	0.25	0.1	3.8

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT115D						97-04-10

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DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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